

Title (en)  
EPITAXIALLY COATED SEMICONDUCTOR WAFER OF MONOCRYSTALLINE SILICON AND METHOD FOR THE PRODUCTION THEREOF

Title (de)  
EPITAKTISCH BESCHICHTETE HALBLEITERSCHEIBE AUS EINKRISTALLINEM SILIZIUM UND VERFAHREN ZU DEREN HERSTELLUNG

Title (fr)  
PLAQUETTE DE SEMI-CONDUCTEUR EN SILICIUM MONOCRISTALLIN, REVÊTU PAR ÉPITAXIE, ET SON PROCÉDÉ DE FABRICATION

Publication  
**EP 3659173 A1 20200603 (DE)**

Application  
**EP 18740798 A 20180712**

Priority  
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• EP 2018068888 W 20180712

Abstract (en)  
[origin: WO2019020387A1] Semiconductor wafer of monocrystalline silicon with a diameter of not less than 300 mm and method for producing a coated semiconductor wafer of monocrystalline silicon. The semiconductor wafer comprises a substrate wafer of monocrystalline silicon and an epitaxial layer of monocrystalline silicon that contains a dopant lying on the substrate wafer, wherein an unevenness of the thickness of the epitaxial layer is no more than 0.5% and an unevenness of the resistivity of the epitaxial layer is no more than 2%.

IPC 8 full level  
**H01L 21/02** (2006.01); **C23C 16/46** (2006.01); **C23C 16/48** (2006.01); **C30B 25/10** (2006.01)

CPC (source: EP IL KR US)  
**C23C 16/24** (2013.01 - IL US); **C23C 16/46** (2013.01 - EP IL KR); **C23C 16/481** (2013.01 - EP IL KR US); **C30B 25/08** (2013.01 - EP IL KR); **C30B 25/105** (2013.01 - EP IL KR US); **C30B 25/165** (2013.01 - EP IL KR); **C30B 25/20** (2013.01 - IL US); **C30B 29/06** (2013.01 - EP IL KR US); **C30B 29/68** (2013.01 - IL US); **H01L 21/02381** (2013.01 - EP IL KR US); **H01L 21/02532** (2013.01 - EP IL KR US); **H01L 21/0262** (2013.01 - EP IL KR US); **H01L 21/02634** (2013.01 - IL US); **H01L 27/14632** (2013.01 - IL); **H01L 27/14687** (2013.01 - IL); **H01L 29/16** (2013.01 - IL US); **H01L 27/14632** (2013.01 - US); **H01L 27/14687** (2013.01 - US)

Citation (search report)  
See references of WO 2019020387A1

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